

REPLACEMENT CLAIMS

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59 (Amended) An integrated circuit substrate formed by a method,  
comprising:

placing said integrated circuit substrate into a reactive chamber;

introducing into said chamber an etching gas;

generating a plasma of said etching gas at a first power level and contacting said  
substrate with said first power level plasma for a first predetermined time; and

generating a plasma of said etching gas at a second power level in said chamber  
and contacting said integrated circuit substrate with said second power level plasma for a  
second predetermined time, wherein said second power level plasma is a higher power  
plasma than said first power level plasma.